Table 3.1 Summary of Important Equations

Quantity	Relationship	Values of Constants and Parameters (for Intrinsic Si at $T = 300$ K)
Carrier concentration in intrinsic silicon (cm^{-3})	$n_i = BT^{3/2}e^{-E_g/2kT}$	$B = 7.3 \times 10^{15}\ \text{cm}^{-3}\text{K}^{-3/2}$ $E_g = 1.12$ eV $k = 8.62 \times 10^{-5}$ eV/K $n_i = 1.5 \times 10^{10}/\text{cm}^3$
Diffusion current density (A/cm^2)	$J_p = -qD_p \dfrac{dp}{dx}$ $J_n = qD_n \dfrac{dn}{dx}$	$q = 1.60 \times 10^{-19}$ coulomb $D_p = 12\ \text{cm}^2/\text{s}$ $D_n = 34\ \text{cm}^2/\text{s}$
Drift current density (A/cm^2)	$J_{\text{drift}} = q(p\mu_p + n\mu_n)E$	$\mu_p = 480\ \text{cm}^2/\text{V}\cdot\text{s}$ $\mu_n = 1350\ \text{cm}^2/\text{V}\cdot\text{s}$
Resistivity ($\Omega \cdot \text{cm}$)	$\rho = 1/[q(p\mu_p + n\mu_n)]$	μ_p and μ_n decrease with the increase in doping concentration
Relationship between mobility and diffusivity	$\dfrac{D_n}{\mu_n} = \dfrac{D_p}{\mu_p} = V_T$	$V_T = kT/q \simeq 25.9$ mV
Carrier concentration in n-type silicon (cm^{-3})	$n_{n0} \simeq N_D$ $p_{n0} = n_i^2/N_D$	
Carrier concentration in p-type silicon (cm^{-3})	$p_{p0} \simeq N_A$ $n_{p0} = n_i^2/N_A$	
Junction built-in voltage (V)	$V_0 = V_T \ln\left(\dfrac{N_A N_D}{n_i^2}\right)$	
Width of depletion region (cm)	$\dfrac{x_n}{x_p} = \dfrac{N_A}{N_D}$ $W = x_n + x_p$ $= \sqrt{\dfrac{2\epsilon_s}{q}\left(\dfrac{1}{N_A} + \dfrac{1}{N_D}\right)(V_0 + V_R)}$	$\epsilon_s = 11.7\epsilon_0$ $\epsilon_0 = 8.854 \times 10^{-14}$ F/cm

Table 3.1 *continued*

Quantity	Relationship	Values of Constants and Parameters (for Intrinsic Si at $T = 300$ K)
Charge stored in depletion layer (coulomb)	$Q_J = q\dfrac{N_A N_D}{N_A + N_D} AW$	
Forward current (A)	$I = I_p + I_n$ $I_p = Aqn_i^2 \dfrac{D_p}{L_p N_D}\left(e^{V/V_T} - 1\right)$ $I_n = Aqn_i^2 \dfrac{D_n}{L_n N_A}\left(e^{V/V_T} - 1\right)$	
Saturation current (A)	$I_S = Aqn_i^2 \left(\dfrac{D_p}{L_p N_D} + \dfrac{D_n}{L_n N_A}\right)$	
I–V relationship	$I = I_S\left(e^{V/V_T} - 1\right)$	
Minority-carrier lifetime (s)	$\tau_p = L_p^2/D_p \qquad \tau_n = L_n^2/D_n$	$L_p, L_n = 1\ \mu\text{m to } 100\ \mu\text{m}$ $\tau_p, \tau_n = 1\ \text{ns to } 10^4\ \text{ns}$
Minority-carrier charge storage (coulomb)	$Q_p = \tau_p I_p \qquad Q_n = \tau_n I_n$ $Q = Q_p + Q_n = \tau_T I$	
Depletion capacitance (F)	$C_{j0} = A\sqrt{\left(\dfrac{\epsilon_s q}{2}\right)\left(\dfrac{N_A N_D}{N_A + N_D}\right)\dfrac{1}{V_0}}$ $C_j = C_{j0}\Big/\left(1 + \dfrac{V_R}{V_0}\right)^m$	$m = \dfrac{1}{3}\ \text{to}\ \dfrac{1}{2}$
Diffusion capacitance (F)	$C_d = \left(\dfrac{\tau_T}{V_T}\right) I$	